

4V Drive Pch MOSFET

RT1E050RP

Structure

Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High power package.
- 3) 4V drive.

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
RT1E050R	0		

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±5	Α
	Pulsed	I _{DP} *1	±20	Α
Source current	Continuous	I _S	-1	Α
(Body Diode)	Pulsed	I _{SP} *1	-20	Α
Power dissipation		P _D *2	1.25	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

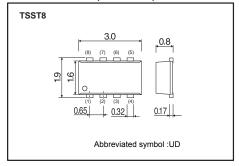
^{*1} Pw \leq 10 μ s, Duty cycle \leq 1%

Thermal resistance

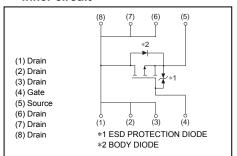
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	100	°C/W

^{*}Mounted on a ceramic board.

• Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μ A	$V_{GS}=\pm20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	I_D =-1mA, V_{GS} =0V
Zero gate voltage drain current	I _{DSS}	ı	1	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	1	-2.5	V	V_{DS} =-10V, I_{D} =-1mA
Static drain course on state	*	ı	26	36		I _D =-5A, V _{GS} =-10V
Static drain-source on-state resistance	R _{DS (on)}	ı	36	50	mΩ	$I_D = -2.5A, V_{GS} = -4.5V$
		1	40	56		$I_D = -2.5A, V_{GS} = -4.0V$
Forward transfer admittance	IY _{fs} ľ	3.1	1	-	S	I _D =-5A, V _{DS} =-10V
Input capacitance	C _{iss}	ı	1300	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	1	180	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	160	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	10	-	ns	I _D =-2.5A, V _{DD} ≒-15V
Rise time	t _r *	ı	15	-	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	ı	90	-	ns	R_L =6.0 Ω
Fall time	t _f *	ı	50	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	13	-	nC	I _D =–5A, V _D =−15V
Gate-source charge	Q _{gs} *	-	3.5	-	nC	V_{GS} =-5 V R_L =3 Ω
Gate-drain charge	Q _{gd} *	-	4.5	-	nC	R_G =10 Ω

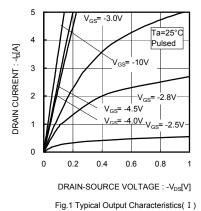
^{*}Pulsed

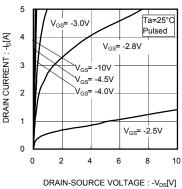
●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^{*}	-	-	-1.2	V	I_s =-5A, V_{GS} =0V

^{*}Pulsed

• Electrical characteristics curves





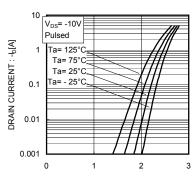
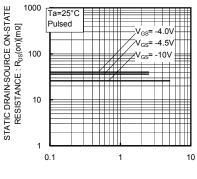


Fig.2 Typical Output Characteristics(II)

 $\label{eq:GATE-SOURCE VOLTAGE:-VGS} GATE-SOURCE \ VOLTAGE:-V_{GS}[V]$ Fig.3 Typical Transfer Characteristics



DRAIN-CURRENT : -b[A]

Fig.4 Static Drain-Source On-State
Resistance vs. Drain Current(I)

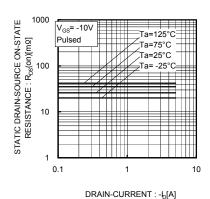


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

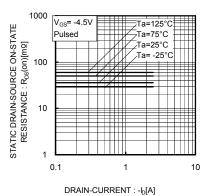


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

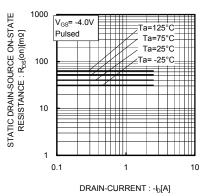


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

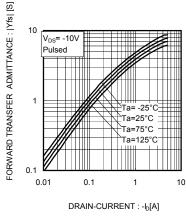


Fig.8 Forward Transfer Admittance vs. Drain Current

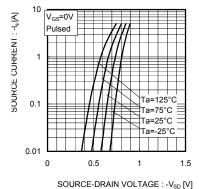
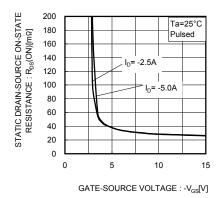
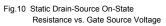


Fig.9 Reverse Drain Current
vs. Sourse-Drain Voltage





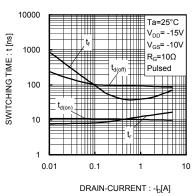


Fig.11 Switching Characteristics

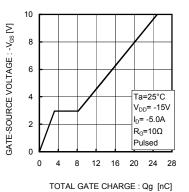


Fig.12 Dynamic Input Characteristics

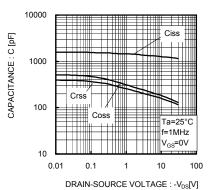


Fig.13 Typical Capacitance vs. Drain-Source Voltage

Measurement circuits

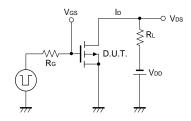


Fig.1-1 Switching Time Measurement Circuit

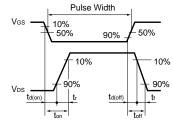


Fig.1-2 Switching Waveforms

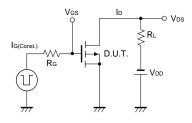


Fig.2-1 Gate Charge Measurement Circuit

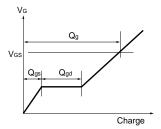


Fig.2-2 Gate Charge Waveform

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